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Observation of the dispersion effect of SnS₂ nanosheets in all-normaldispersion Yb-doped mode-locked fiber laser



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ABSTRACT

In the present study, the dispersion effect of SnS_2 nanosheets was investigated by comparing two groups of data that produced by all-normal-dispersion Yb-doped mode-locked fiber laser with SnS_2 nanosheets or not. Besides, the nonlinear saturable absorption characteristics of the SnS_2 were investigated experimentally. The saturation intensity and modulation depth were $6.01 \, \text{MW/cm}^2$ and 8.68%, respectively. The dispersion effect of SnS_2 nanosheets significantly decreased pulse width. The pulse duration was shortened to one half or one third of the original. When the pump power was 193.3 mW, the narrowest pulse width was 1.05 ns. In this study, the dispersion effect of SAs was first observed and experimentally investigated in an all-normal-dispersion laser cavity. Based on the results here, a new method can be developed to investigate passively mode-locked fiber laser and promote the practical applications of SAs in the field of ultrafast photonics.

1. Introduction

In recent years, mode-locked fiber lasers have aroused huge attention for their useful practicability in many areas, e.g. optical communication, micromachining, metrology and military systems [1-4]. Passively mode-locked fiber lasers have been extensively investigated for many of their advantages, e.g. compact structure, low cost, simplicity and the flexibility of their design [5-7]. Thus far, various types of saturable absorbers (SAs), e.g. semiconductor saturable absorption mirror (SESAM) [8,9], graphene [10-14], carbon nanotubes [15-18], topological insulators [19-25], transition metal dichalcogenides (TMDs) [26–36], and black phosphorus [37–40], have been adopted to achieve passive mode-locked lasers. For instance, Guo et al. demonstrated a sub-200 fs soliton mode-locked erbium-doped fiber laser (EDFL) using a microfiber-based bismuthene saturable absorber [40]. Bi₂Se₃ was successfully used for demonstrating a large-energy passively Q-switched erbium-doped fiber laser in 2019 [25]. Moreover, various TMDs, with the advantages of ultrafast recovery time, unusual electronic, structural properties and wide absorption, have been broadly used to achieve mode-locked or Q-switched fiber laser. Recently, IV-VI group TMDs, covering ReS2 and SnS2, have also aroused considerable interest. For instance, Mao et al. reported a ReS2-polyvinyl alcohol (PVA) film based passively Q-switched and mode-locked erbium-doped fiber lasers [41].

Niu et al. have investigated the nonlinear absorption property of $\rm SnS_2$ and achieved a passively Q-switched Er-doped fiber laser with minimum pulse width of 510 ns [42]. Besides, $\rm SnS_2$ -PVA film was successfully prepared and employed as a mode-locker in obtaining an Er-doped modelocked laser with a pulse width of 623 fs in 2018 [43].

The saturation absorption characteristics of above materials were experimentally and theoretically verified. Except the saturation absorption characteristics of materials, the characteristics of the laser system can be affected by dispersion, linear gain and loss, spectral filtering and nonlinear effect. Some researches studied special modelocked laser phenomena by adjusting dispersion in laser system. Lin et al. experimentally investigated the bound states of multiple dispersion-managed solitons (DMSs) from a net-normal-dispersion passive mode-locked Yb-doped fiber laser [44]. Cheng et al. achieved dissipative soliton resonance in an all-normal-dispersion mode-locked Ybdoped fiber laser [45]. Nevertheless, the dispersion effect of SAs in fiber laser system has not been investigated. Accordingly, this study first investigated the dispersion effect of SAs in an all-normal-dispersion passively mode-locked ytterbium-doped fiber laser at 1064 nm. Moreover, tin disulfide (SnS2) was used to study its dispersion effect for laser system. SnS₂ was an n-type direct bandgap semiconductor with a value of 2.24 eV. It exhibits a CdI2 crystal structure with the sandwich structure, which is composed by two layers of close-packed sulfur

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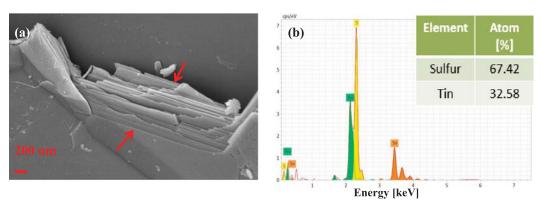
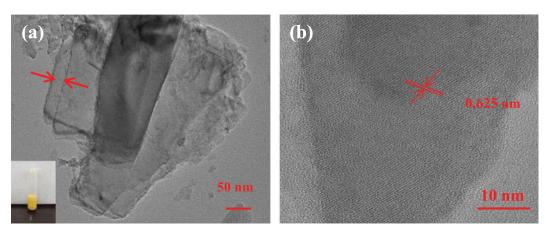


Fig. 1. (a) The SEM image of the SnS2 nanosheets. (b) EDX spectroscopy of the SnS2 nanosheets, inset: the atomic ratio of sulfur and tin.



 $\textbf{Fig. 2.} \ \, \textbf{(a)} \ \, \textbf{The TEM image of the SnS}_2 \ \, \textbf{nanosheets. (b)} \ \, \textbf{The HTEM image of the SnS}_2 \ \, \textbf{nanosheets. Inset of (a)} \ \, \textbf{The SnS}_2 \ \, \textbf{dispersion solution.}$

anions and one-layer tin cations [46–49]. Besides, the advantages of SnS_2 are low-cost, environmentally friendly and Earth-abundant, which made it better to fulfill scientific and industrial requirements.

For the first time, this study investigated the dispersion characteristics of the $\rm SnS_2$ nanosheets in an all-normal-dispersion passively mode-locked Yb-doped fiber laser by contrasting the data that were produced by the all-normal-dispersion Yb-doped fiber laser with $\rm SnS_2$ nanosheets or not. Besides, the nonlinear saturable absorption characteristics of the $\rm SnS_2$ were investigated experimentally. The saturation intensity and modulation depth were about 6.01 MW/cm² and 8.68%, respectively. This study found that the dispersion effect of $\rm SnS_2$ nanosheets significantly decreases pulse width. The pulse duration was shortened to one half or one third of the original. The narrowest pulse width was 1.05 ns under the pump power of 193.3 mW. Based on these results, a new method can be developed to investigate mode-locked fiber laser, which will promote the practical applications of SAs in the field of ultrafast photonics.

2. Preparation and characterization of materials

The preparation process of the SA is to be described as follow steps. Adding 1 g SnS_2 nanosheets into $100\,mL$ alcohol (30%) is the first step to prepare a SnS_2 dispersion solution. To fully mix the SnS_2 dispersion solution still need to be placed in the ultrasonic cleaner for $12\,h$. Second, 5 wt% PVA solution and the SnS_2 dispersion solution were mixed at the volume ratio of 3:2. The SnS_2 -PVA dispersion solution was produced by cleaning mixture dispersion solution using the ultrasonic cleaner for $4\,h$. Third, $180\,\mu L$ SnS_2 -PVA dispersion solution was spin-coated on a sapphire substrate to format the SnS_2 -PVA film. Finally, a $1\times 1\,mm^2$ thin film was cut off and put on the end face of the photonic crystal (PC) fiber head as SAs.

The structure of SnS₂ nanosheets was analyzed by using following characterizations. The surface topography of the SnS₂ nanosheets was observed and analyzed under a scanning electron microscope (SEM). As

shown in Fig. 1(a), SEM image shows that SnS_2 nanosheets have a layered structure with a resolution of 200 nm. The elemental composition and stoichiometry of the SnS_2 nanosheets were analyzed using the energy dispersion X-ray (EDX). The corresponding peaks associated with sulfur and tin are observed clearly shown in Fig. 1(b). The inset of Fig. 1(b) suggests the atomic ratio of sulfur (67.42%) and tin (32.58%) was estimated to be 2:1.

A JEM-2100 microscope with an optical resolution of 50 nm was used to record the transmission electron microscope (TEM) image of the SnS_2 nanosheets dispersion solution. SnS_2 exhibits layered structure, as clearly shown in Fig. 2(a). The inset of Fig. 2(a) suggests that SnS_2 dispersion solution is uniform yellow dispersion solution. Subsequently, high crystallinity of this SnS_2 dispersion solution could be demonstrated by the regular diffraction fringes (HRTEM, Fig. 2(b)), with the lattice spacing of 0.625 nm.

Furthermore, the structure characterizations of the SnS_2 nanosheets were also investigated using the X-ray diffraction (XRD) technology and the Raman spectrum [50]. As shown in Fig. 3(a), the peaks were recorded, corresponding to the (0 0 1), (1 0 0), (0 0 2), (1 0 1), (1 0 2) and (0 0 3) planes in SnS_2 . The high diffraction peaks at (0 0 1) plane in the XRD pattern is obvious, which reveals that the SnS_2 nanosheets prepared exhibit well-layered structure and high crystallinity [43]. Two Raman shift peaks can be observed in Fig. 3(b), corresponding to the A_{1g} and E_g symmetry intralayer mode at 313.04 and 203.79 cm $^{-1}$, which is consistent with the previously reported results [49].

The thickness characteristics of the prepared SnS_2 nanosheets were measured with an atomic force microscope (Bruker Multimode 8). In Fig. 4(a), four areas were used to analyze the height of SnS_2 nanosheets

 $^{^{\}rm 1}$ For interpretation of color in Fig. 2, the reader is referred to the web version of this article.

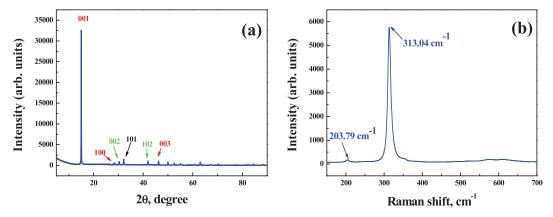


Fig. 3. (a) X-ray diffraction of the SnS2 nanosheets. (b) Raman spectrum of the SnS2 nanosheets.

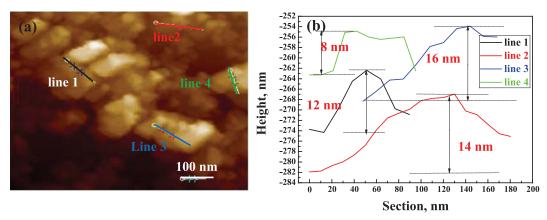


Fig. 4. (a) The AFM image of the SnS₂ nanosheets. (b) The height measurement of the selected-area in Fig. 4(a).

under the resolution of 100 nm. The thickness of these areas were measured as 8, 12, 14 and 16 nm, respectively, as shown in Fig. 4(b). Based on a predicted monolayer thickness of $\approx 0.6 \,\mathrm{nm}$ [51], the layer number of the SnS2 nanosheets in the experiment was estimated at nearly 13-26.

Using a power-dependent transmission technique, the nonlinear absorption property of the SnS2-PVA film-type SA was investigated [52]. The experimental results are shown in Fig. 5(a). Besides, the data were fitted to the following equation [30]:

$$T(I) = 1 - T_{ns} - \Delta T \times exp(-I/I_{sat})$$

where T denotes transmission, T_{ns} is non-saturable absorbance, ΔT is modulation depth, I is input intensity of laser, and I_{sat} is saturation intensity. The intensity and modulation depth were obtained as 6.01 MW/cm² and 8.68%, respectively, by fitting the experimental results. In Fig. 5(b), a UV/Vis/NIR spectrophotometer (Hitachi U-4100) was used to investigate the transmittance of the SnS2-PVA film and the substrate versus optical wavelength. It can be clearly observed that the transmission increases with the wavelength. Moreover, the transmission of the SnS2-PVA film at the wavelength of 1027 nm was about 73.46%.

3. Experimental details

The experimental setup of the SnS2 nanosheets in all-normal-dispersion Yb-doped mode-locked fiber laser is shown in Fig. 6. A piece of 0.3 m Yb-doped fiber (LIEKKI Yb1200-4/125) as the laser gain medium with group velocity dispersion (GVD) of 24.22 ps²/km was pumped

(b)

1800

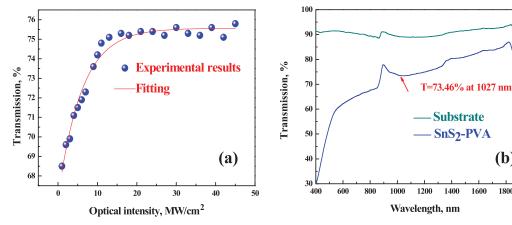


Fig. 5. (a) Nonlinear absorption property of the SnS2-PVA film. (b) Linear transmission of the SnS2-PVA film versus wavelength.

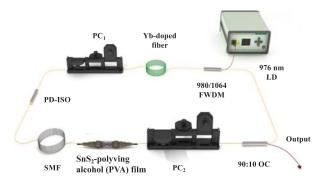


Fig. 6. Experimental setup of the noise-like mode-locked fiber laser.

using 976 nm laser diode (LD) with a 980/1064 nm filter wavelength division multiplexer (FWDM). Two polarization controllers (PCs) were used to adjust the polarization state in the cavity. A polarization-dependent isolator (PD-ISO) was used to transform the common light into linearly polarized lights, which demonstrates the mode-locked pulse output. A piece of 303.08 m long single-mode fiber (SMF-28) with GVD of 17.7 ps²/km was adopted to increase the Kerr nonlinearity and adjust dispersion in cavity. The laser output beam was extracted through the 10% output port of a 10:90 output optical coupler (OC). The total cavity length was up to 303.38 m, suggesting that the net dispersion of the Yb-doped fiber laser was estimated at nearly 5.37 ps². The output performances of the fiber laser were recorded using a fast-speed photodetector (3G), a digital oscilloscope (DPO4054), a power meter (PM100DS122C), an optical spectrum analyzer (AQ6317) and a spectrum analyzer (R&S FPC1000).

4. Experimental results

Fig. 7(a) shows the output power and the pulse duration as a function of pump power in a mode-locked fiber laser without SA, only including PD-ISO and SMF. When the pump power increased from 44.5 to 226.4 mW, the pulse duration increased from 2.75 to 4.1 ns, the narrowest pulse duration was 2.2 ns under a pump power of 79 mW. The value of pulse duration would decrease under the pump power above 226.4 mW. Because the nonlinear effect of the fiber would be improved under the high pump power. In the meantime, when the pump power rose from 44.8 to 319.7 mW, the output power increased was up-regulated 0.402–5.15 mW. Fig. 7(b) suggests that, the output power and the pulse duration acted as a function of pump power in a mode-locked fiber laser, which includes PD-ISO, SMF and SnS₂-PVA film. When pump power increased from 53.1 to 193.3 mW, the output power rose from 0.173 to 1.023 mW. The pulse duration was reduced

from 1.7 to 1.05 ns, and the narrowed pulse duration was 1.05 ns under a pump power of 193.3 mW. The value of the pulse duration would increase under the pump power above 193.3 mW. By comparing the data in above graphs, the pulse duration is found compressed after added the SnS₂-PVA film. The pulse duration was shorted to one half or one third of the original. Cheng et al. have demonstrated reduce the length of the SMF can effectively decrease the pulse width, which attributed to the cavity dispersion is changed [41]. Therefore, in this study, the phenomenon of pulse duration shorted was also attributed to the change of cavity dispersion. Due to the length of the SMF not change, therefore, we concluded the phenomenon was attributed to the dispersion effect of the SnS₂-PVA film. To the best of our knowledge, this study initially investigated the dispersion characteristics of the SAs in all-normal-dispersion passively mode-locked Yb-doped fiber laser.

As shown in Fig. 8(a), the single pulse train of the mode-locked fiber laser without SA under the pump power of 319.7 mW was recorded, with the full width high maximum (FWHM) of 2.5 ns. The inset was multi-pulse train under the same pump power. Besides, in Fig. 8(b), the single pulse train of the mode-locked fiber laser with SA under the pump power of 214 mW was recorded, with the FWHM of 1.55 ns. The multi-pulse train was also recorded and shown in the inset of Fig. 8(b).

Besides, stability is one of the critical parameters of passively modelocked fiber laser. To characterize the stability of the mode-locked fiber laser, a spectrum analyzer (R&S FPC1000) was employed to record the radio frequency spectrum. The radio frequency (RF) spectrum of the mode-locked fiber laser without SA was recorded, as shown in Fig. 9(a). The radio frequency spectrum located at a fundamental repetition rate of 677.6 kHz, with a bandwidth of 1400 kHz, a resolution of 300 Hz, and the single-to-noise ratio of 28 dB. The radio frequency spectrum within a wide bandwidth of 18 MHz is shown in the inset of Fig. 9(a). The radio frequency (RF) spectrum of the mode-locked fiber laser with SnS₂-PVA film was recorded, as shown in Fig. 9(b). The radio frequency spectrum located at a fundamental repetition rate of 675.1 kHz with a bandwidth of 1400 kHz and a resolution of 300 Hz, the single-to-noise ratio is 40 dB. The radio frequency spectrum within a wide bandwidth of 18 MHz is shown in the inset of Fig. 9(b). This study found that the single-to-noise ratio was improved after adding the SnS2-PVA film, which implies that the stability of the mode-locked pulse was improved.

In Fig. 10(a), the typical dual-wavelength emission spectrum of the mode-locked fiber laser without SA was recorded using an optical spectrum analyzer (AQ-6317) under a resolution of 0.02 nm. An obvious dual-wave-length spectrum located at 1031.08 and 1034.19 nm was clearly observed. The emission spectrum of the mode-locked fiber laser with SnS₂-PVA film is shown in Fig. 10(b). The central wavelength and 3 dB bandwidth reached 1027.71 and 0.064 nm, respectively.

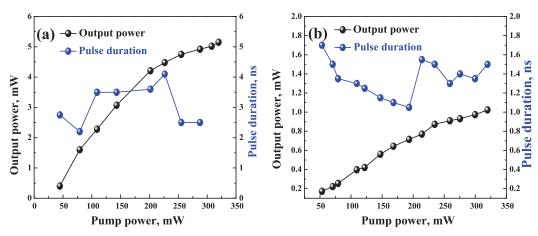


Fig. 7. (a) PD-ISO and SMF: The output power and the pulse duration as a function of pump power. (b) PD-ISO, SMF and SnS₂-PVA film: The output power and the pulse duration as a function of pump power.

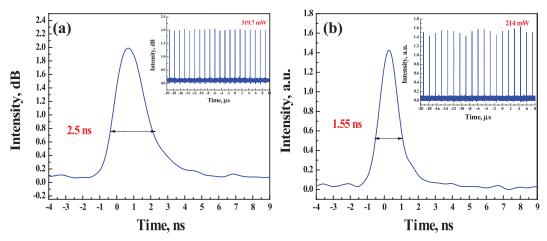


Fig. 8. (a) PD-ISO and SMF: single pulse train and multi-pulse train recorded with oscilloscope under the pump power of 319.7 mW; (b) PD-ISO, SMF and SnS₂-PVA film: single pulse train and multi-pulse train recorded with oscilloscope under the pump power of 214 mW.

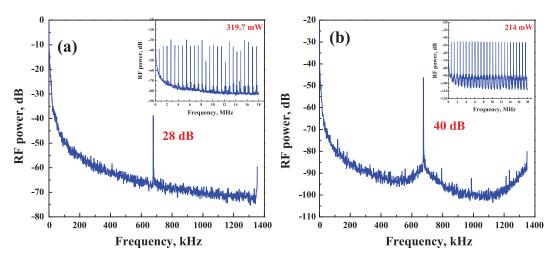


Fig. 9. (a) PD-ISO and SMF: RF spectrum of the mode-locked YDFL at pump power of 319.7 mW. Inset is RF spectrum with 18 MHz. (b) PD-ISO, SMF and SnS₂-PVA film: RF spectrum of the mode-locked YDFL at pump power of 214 mW. Inset is RF spectrum with 18 MHz.

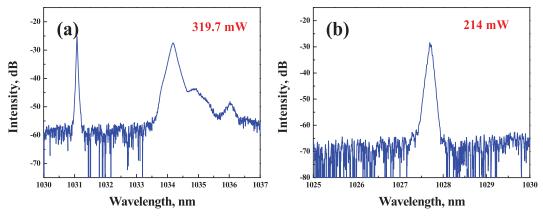


Fig. 10. (a) PD-ISO and SMF: Emission spectrum. (b) PD-ISO, SMF and SnS₂-PVA film: Emission spectrum.

5. Conclusion

To sum up, this study initially investigated the dispersion effect of the SnS_2 -PVA film in an all-normal-dispersion passively mode-locked Yb-doped fiber laser. We found that the dispersion effect of SnS_2 nanosheets significantly decreased pulse width. By compressing, the narrowest pulse width was 1.05 ns under the pump power of 193.3 mW.

The results here demonstrated that the dispersion effect of the SAs is worth investigating, which will facilitate the practical applications of SAs in ultrafast photonics.

Declaration of Competing Interest

There is no conflict of interest.

Acknowledgements

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